



GPD Optoelectronics Corp.

7 Manor Parkway

Salem, NH 03079

U.S.A.

Tel: (603) 894-6865

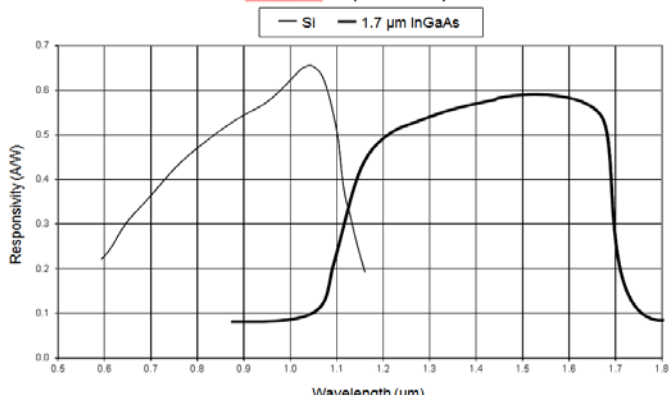
Fax: (603) 894-6866

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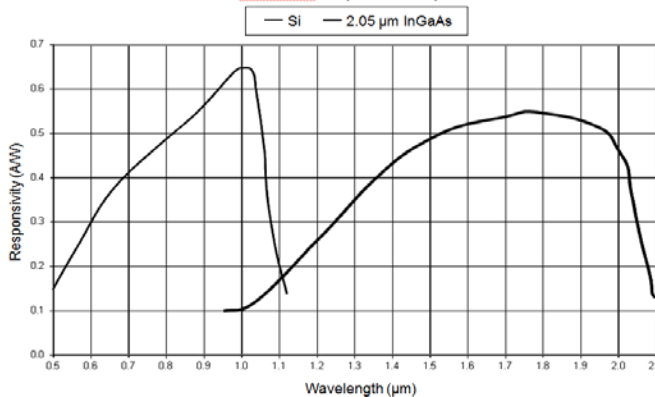
Si/InGaAs Two-Color Sensor

Type	Active Diameter (mm)	Wavelength Range (μm)	Peak Responsivity (A/W)	Minimum Shunt Resistance (MΩ)	NEP (pW/Hz ^{1/2})	Max Leakage Current (μA)	Max Reverse Bias (V)
Si GAP9096-1	2.6 x 2.6	0.4 - 1.0	0.550	200.000	0.020	0.002 @ 10 V	50.000
InGaAs	1.000	1.0 - 1.7	0.550	20.000	0.050	0.01 @ 1 V	20.000
Si GAP9096-2	2.6 x 2.6	0.4 - 1.0	0.55	200	0.02	0.002 @ 10 V	50
InGaAs	1	1.1 - 2.05	0.55	0.6	0.3	9 @ 1 V	2
Si GAP9096-3	2.6 x 2.6	0.4 - 1.0	0.55	200	0.02	2 @ 10 V	50
InGaAs	1	1.1 - 2.2	0.55	0.025	1.5	20 @ 1 V	2
Si GAP9096-4	2.6 x 2.6	0.4 - 1.0	0.55	200	0.02	2 @ 10 V	50
InGaAs	1	1.1 - 2.6	0.55	0.002	5	25 @ 1 V	1

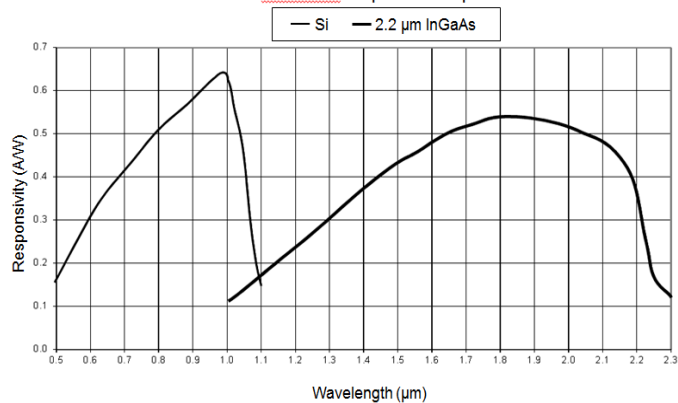
GAP9096-1 Spectral Response



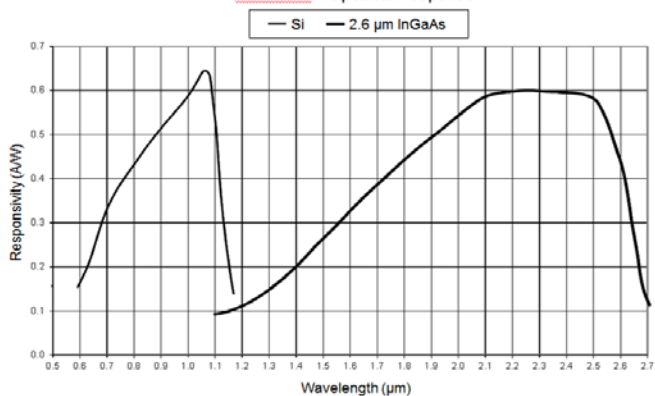
GAP9096-2 Spectral Response

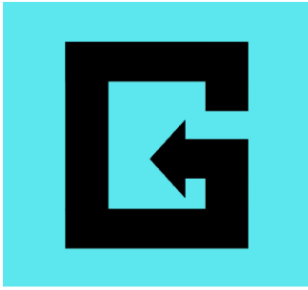


GAP9096-3 Spectral Response



GAP9096-4 Spectral Response





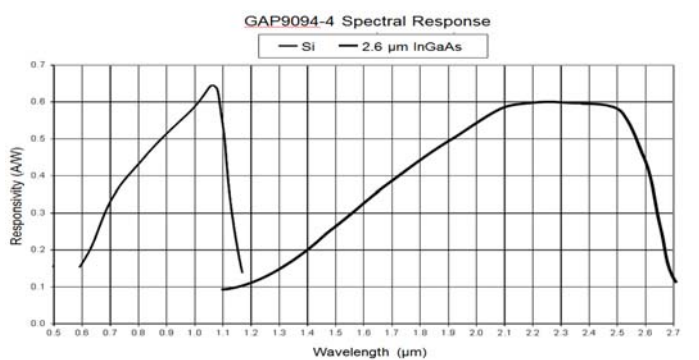
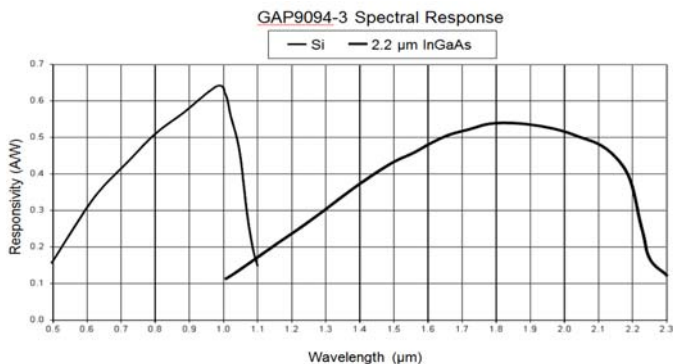
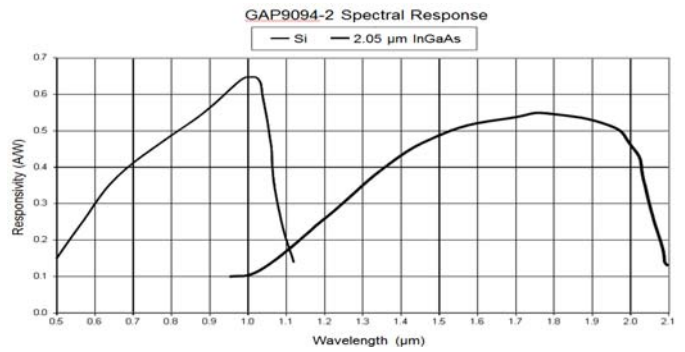
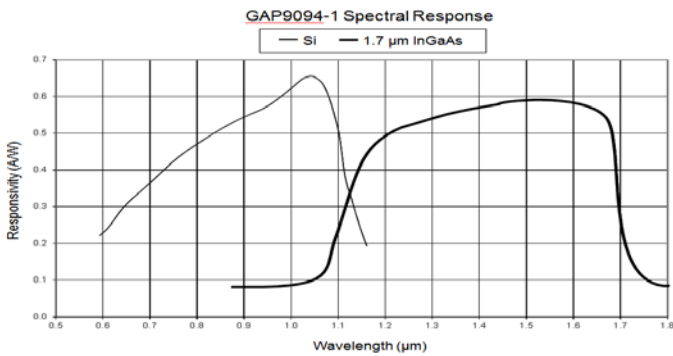
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Si/InGaAs Two-Color Sensor

Type	Active Diameter (mm)	Wavelength Range (μm)	Peak Responsivity (A/W)	Minimum Shunt Resistance (MΩ)	NEP (pW/Hz ^{1/2})	Max Leakage Current (μA)	Max Reverse Bias (V)
Si GAP9094-1	2.6 x 2.6	0.4 - 1.0	0.55	200	0.020	0.002 @ 10 V	50
InGaAs	2	1.0 - 1.7	0.55	5	0.050	0.1 @ 1 V	5
Si GAP9094-2	2.6 x 2.6	0.4 - 1.0	0.55	200	0.02	0.002 @ 10 V	50
InGaAs	2	1.1 - 2.05	0.55	0.02	1.6	30 @ 1 V	2
Si GAP9094-3	2.6 x 2.6	0.4 - 1.0	0.55	200	0.02	0.002 @ 10 V	50
InGaAs	2	1.1 - 2.2	0.55	0.006	3	50 @ 1 V	1
Si GAP9094-4	2.6 x 2.6	0.4 - 1.0	0.55	200	0.02	0.002 @ 10 V	50
InGaAs	2	1.1 - 2.6	0.55	500 Ω	10	50 @ 0.5 V	0.5





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InGaAs/InGaAs Two-Color Sensor

Type	Active Diameter (mm)	Wavelength Range (μm)	Peak Responsivity (A/W)	Minimum Shunt Resistance ($\text{M}\Omega$)	NEP ($\text{pW}/\text{Hz}^{1/2}$)	Max Leakage Current (μA)	Max Reverse Bias (V)
InGaAs GAP9099	2	0.8 - 1.5	0.9 @ 1.55 μm	5	0.06	0.2 @ 1 V	3
InGaAs	2	1.5 - 1.75	0.15 @ 1.68 μm	5	0.38	0.2 @ 1 V	3
InGaAs GAP9116-1	2	0.8 - 1.75	0.9 @ 1.55 μm	5	0.06	0.2 @ 1 V	3
InGaAs	2	1.5 - 2.1	0.45 @ 1.90 μm	0.04	1.4	50 @ 1 V	1
InGaAs GAP9116-2	2	0.8 - 1.75	0.9 @ 1.55 μm	5	0.06	0.2 @ 1 V	3
InGaAs	2	1.5 - 2.2	0.45 @ 2.0 μm	0.006	3.4	50 @ 0.5 V	1
InGaAs GAP9116-3	2	0.8 - 1.75	0.9 @ 1.55 μm	5	0.06	0.2 @ 1 V	3
InGaAs	2	1.5 - 2.6	0.5 @ 2.4 μm	800 Ω	9	80 @ 0.5 V	1

